

E. Compound Semiconductors 분과

2017년 2월 14일 (화), 16:00-17:30
Room D (크리스탈, 2층)

[TD3-E] WBG Power Device

좌장: 문재경(한국전자통신연구원), 장태훈(전북대학교)

TD3-E-1 16:00-16:15	PECVD SiON for Normally-off AlGaIn/GaN-on-Si Recessed MIS-HFETs Hyun-Seop Kim ¹ , Sang-Woo Han ¹ , Won-Ho Jang ¹ , Kwang-Seok Seo ² , and Ho-Young Cha ¹ <i>¹School of Electronic and Electrical Engineering, Hongik University, ²Department of Electrical Engineering and Computer Science, Seoul National University</i>
TD3-E-2 16:15-16:30	Normally-off GaN-based MOSFET realized by TMAH Solution for both Selective Recess and Etch Stop Processes Dong-Hyeok Son, Young-Woo Jo, Won-Sang Park, Chan Heo, Chul-Ho Won, Dai Quan, Jeong-Gil Kim, Jae Hwa Seo, In Man Kang, and Jung-Hee Lee <i>School of electronics engineering, Kyungpook National University</i>
TD3-E-3 16:30-16:45	Study for Reliability of Threshold Voltage in E-Mode AlGaIn / GaN MOS-HEMT with Al₂O₃ Dielectric Il-Hwan Hwang ¹ , Kwang-Ho Choi ¹ , Ho-Young Cha ² , and Kwang-Seok Seo ¹ <i>¹Seoul national University and ISRC. Department of Electrical and Computer Engineering, ²Hongik University. Electronic and Electrical Engineering</i>
TD3-E-4 16:45-17:00	600 V/10A GaN Power Transistors for High Efficiency and Power Density Hyung-Seok Lee, Hyun-Gyu Jang, Jeho Na, JinSig Kim, Seong-Bum Bae, Woojin Chang, Eunsoo Nam, and Jae-Kyoung Mun <i>GaN Power Electronics Research Section, Electronics and Telecommunications Research Institute</i>
TD3-E-5 17:00-17:15	A Low Forward Voltage Drop of 4H-SiC TSBS Employing Poly-Si/Ni Dual Metals 김동영 ^{1,2} , 박힘찬 ² , 방욱 ² , 박기철 ¹ , 석오균 ² <i>¹경상대학교 반도체 공학과, ²한국전기연구원 전력반도체연구센터</i>
TD3-E-6 17:15-17:30	Investigation of Threshold Voltage Variation under Negative-Bias Stress Condition of SiC Double-Implanted MOSFETs Sangwon Baek ¹ , Bo Jin ¹ , Junyoung Lee ¹ , Jiwon Kim ¹ , Hyeongwan Oh ¹ , Chanoh Park ² , Donghoon Kim ¹ , and Jeong-Soo Lee ¹ <i>¹Department of Electrical Engineering, Pohang University of Science and Technology, ²Division of IT Convergence Engineering, Pohang University of Science and Technology</i>